



## PATENT ABSTRACTS OF JAPAN

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**G03F 7/26**(21) Application number: **05173505**(22) Date of filing: **14.07.1993**(71) Applicant: **OKI ELECTRIC IND CO LTD**(72) Inventor: **ITO YOSHIO**(54) **RESIST PATTERN FORMING METHOD**

## (57) Abstract:

**PURPOSE:** To provide a resist pattern forming method with which the thinning of top film by the effect of defocus and the roundness of bottom part can be eliminated simultaneously by a method wherein the resists having a different solubility are formed in a multilayer structure such as a two-layer structure, for example, when a developing operation is conducted after exposing treatment.

**CONSTITUTION:** The resist pattern forming method used in the photolithography process for manufacture of a semiconductor device, includes the steps of forming a photoresist film in a multilayer structure consisting of a lower layer resist thin film 11 and an upper layer resist thin film 12 having different solubilities when de-

veloping after exposing treatment, and effecting exposure for formation of a circuit pattern on the multistructure photoresist film. The photoresist film of multilayer structure is developed in such a manner that the photoresist thin film 12, to be formed as the upper layer, has a solubility at developing lower than that of the photoresist film 11 of the lower layer for the same exposure.

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